- Readme notice
  1. 只用电池供电,电池规格Li-3.7V
  2. USB隔离,保护电源,降低工频
  3. 5340内电源只用VDD,不使用VDDH原理图参考手册P805

## 9.3.2 Circuit configuration no. 2 for QKAA aQFN94

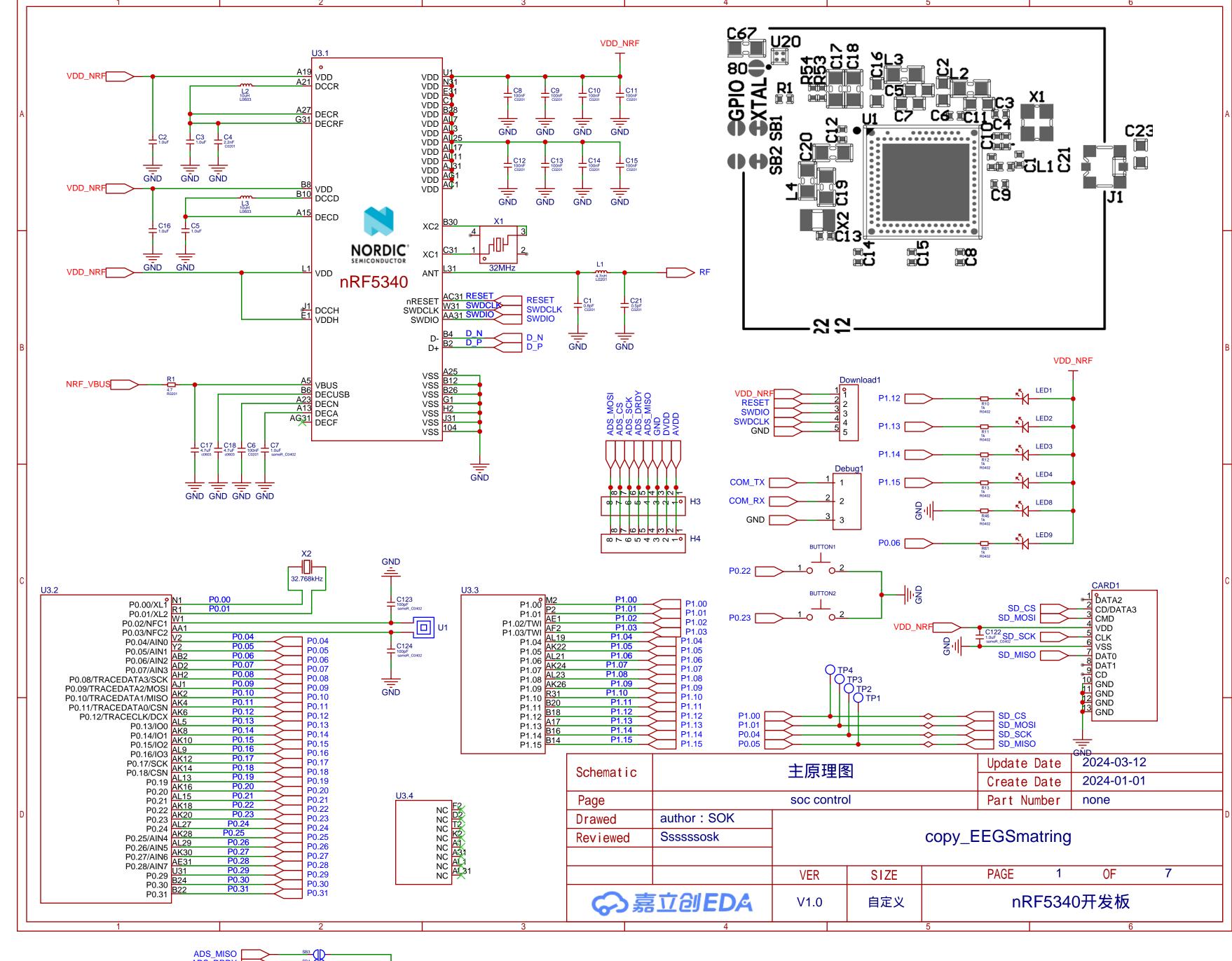
Circuit configuration number 2 for QKAA aQFN94 is showing the schematic and the bill of materials table.

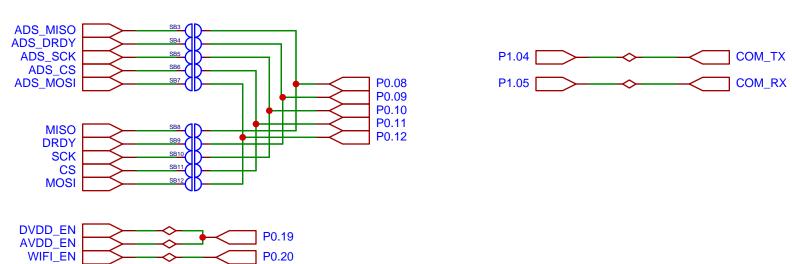
Config no.	Supply configuration		Enabled features				
	VDDH	VDD	EXTSUPPLY	DCDC on VREGH	DCDC on VREGMAIN and VREGRADIO	USB	NFC
Config. 2	N/A	Battery/Ext. regulator	No	No	Yes	Yes	Yes

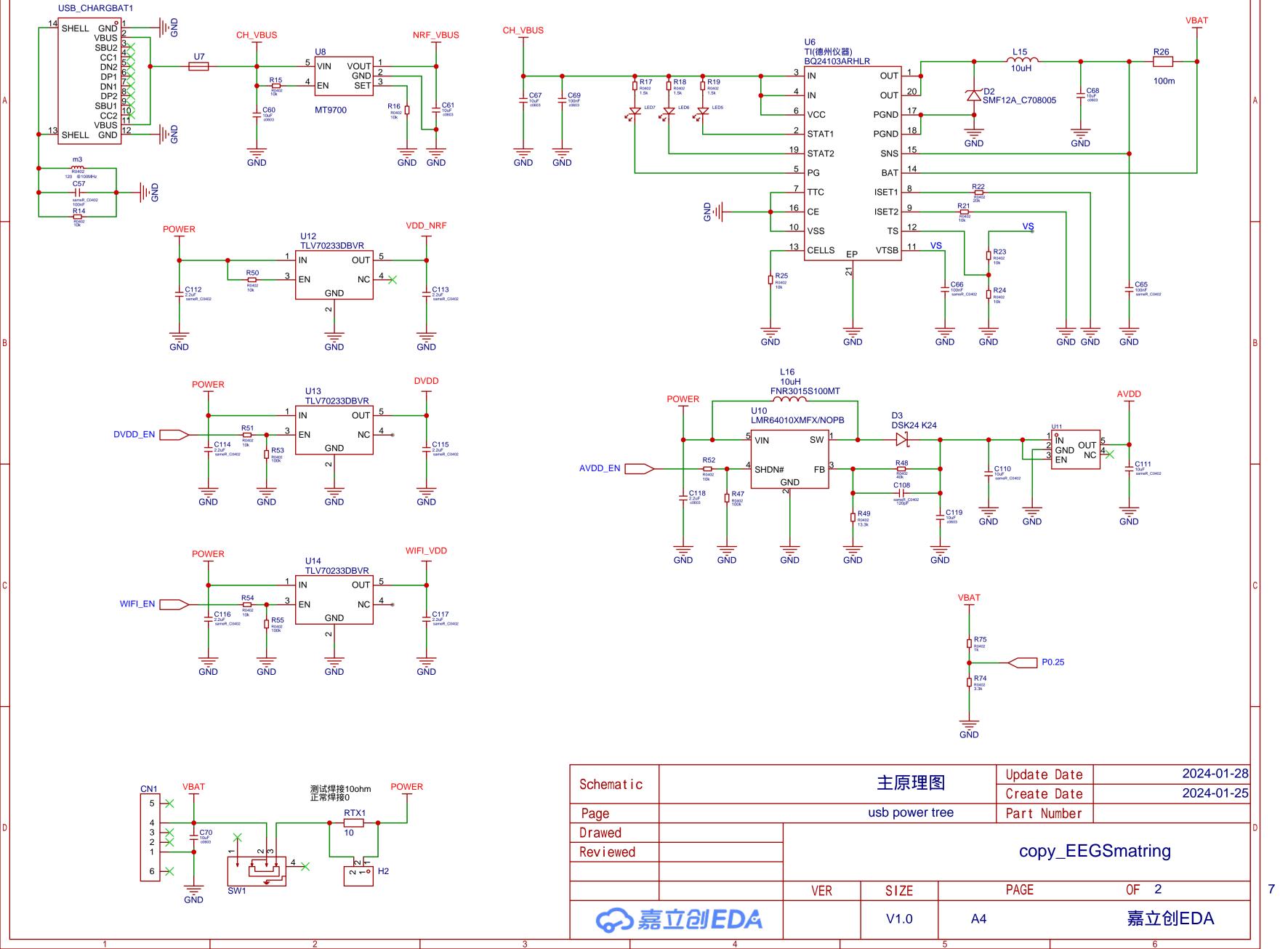
Table 218: Configuration summary for circuit configuration no. 2

Designator	Value	Description	Footprint
C1	0.7 pF	Capacitor, NPO, ±0.05 pF	0201
C2, C3, C5, C7, C16	1.0 μF	Capacitor, X7S, ±10%	0402
C4	2.2 nF	Capacitor, X7R, ±10%	0201
C6, C8, C9, C10, C11, C12, C13, C14, C15	100 nF	Capacitor, X7S, ±10%	0201
C17	4.7 μF	Capacitor, X7S, ±10%	0603
C18	4.7 μF	Capacitor, X7R, ±10%	0603
C21	N.C.	Not mounted	0201
CT1, CT2, CT3, CT4	Antenna dependent	Capacitor, NPO, ±5%	0201
L1	2.2 nH	High frequency chip inductor, ±5%	0201
L2, L3	10 μΗ	Inductor, 50 mA, ±20%	0603
R1	2.2 Ω	Resistor, ±1%, 0.05 W	0201
U1	nRF5340- QKAA	Multiprotocol Bluetooth Low Energy, IEEE 802.15.4, ANT, and 2.4GHz proprietary System on Chip	AQFN-94
X1	32 MHz	Crystal SMD 2016, 32 MHz, Cl=8 pF, Total Tol: ±30 ppm. For frequency tolerance requirements, see 32 MHz crystal oscillator (HFXO) on page 102.	XTAL_2016
X2	32.768 kHz	Crystal SMD 2012, 32.768 kHz, Cl=9 pF, Total Tol: ±50 ppm	XTAL_2012

Table 219: Bill of material for circuit configuration no. 2







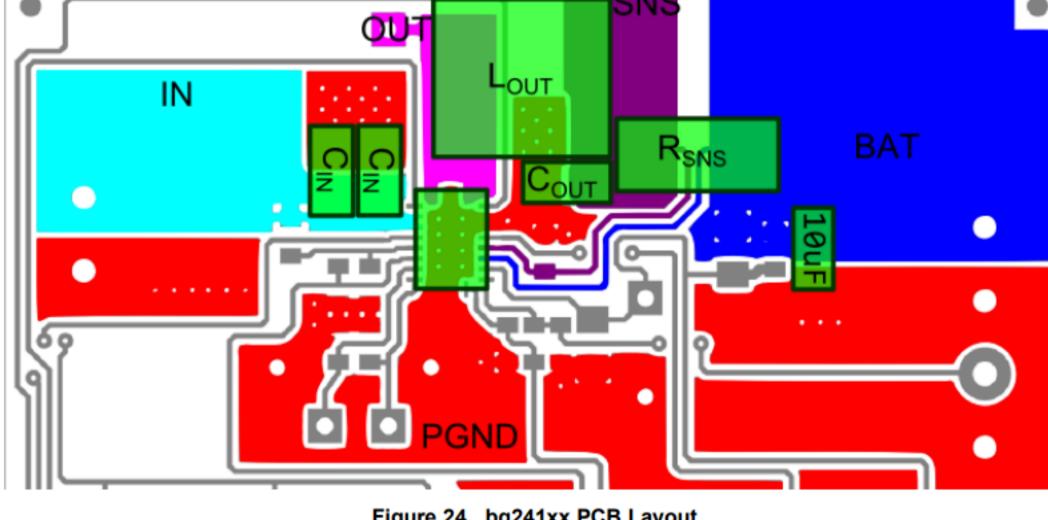
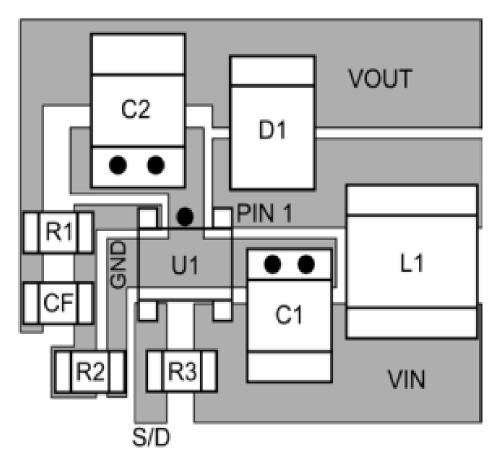
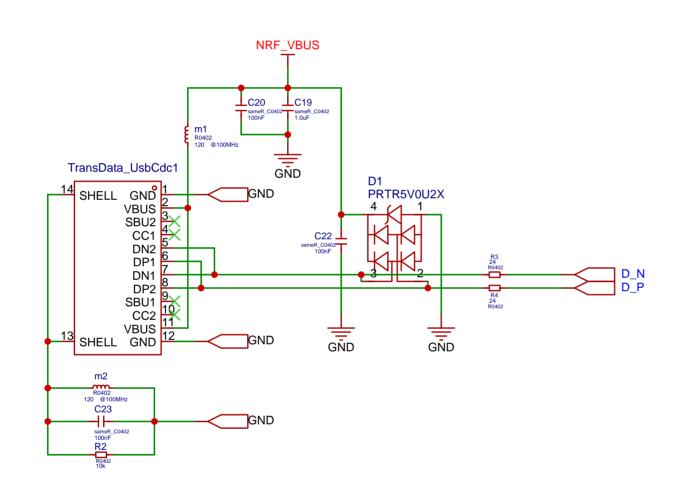
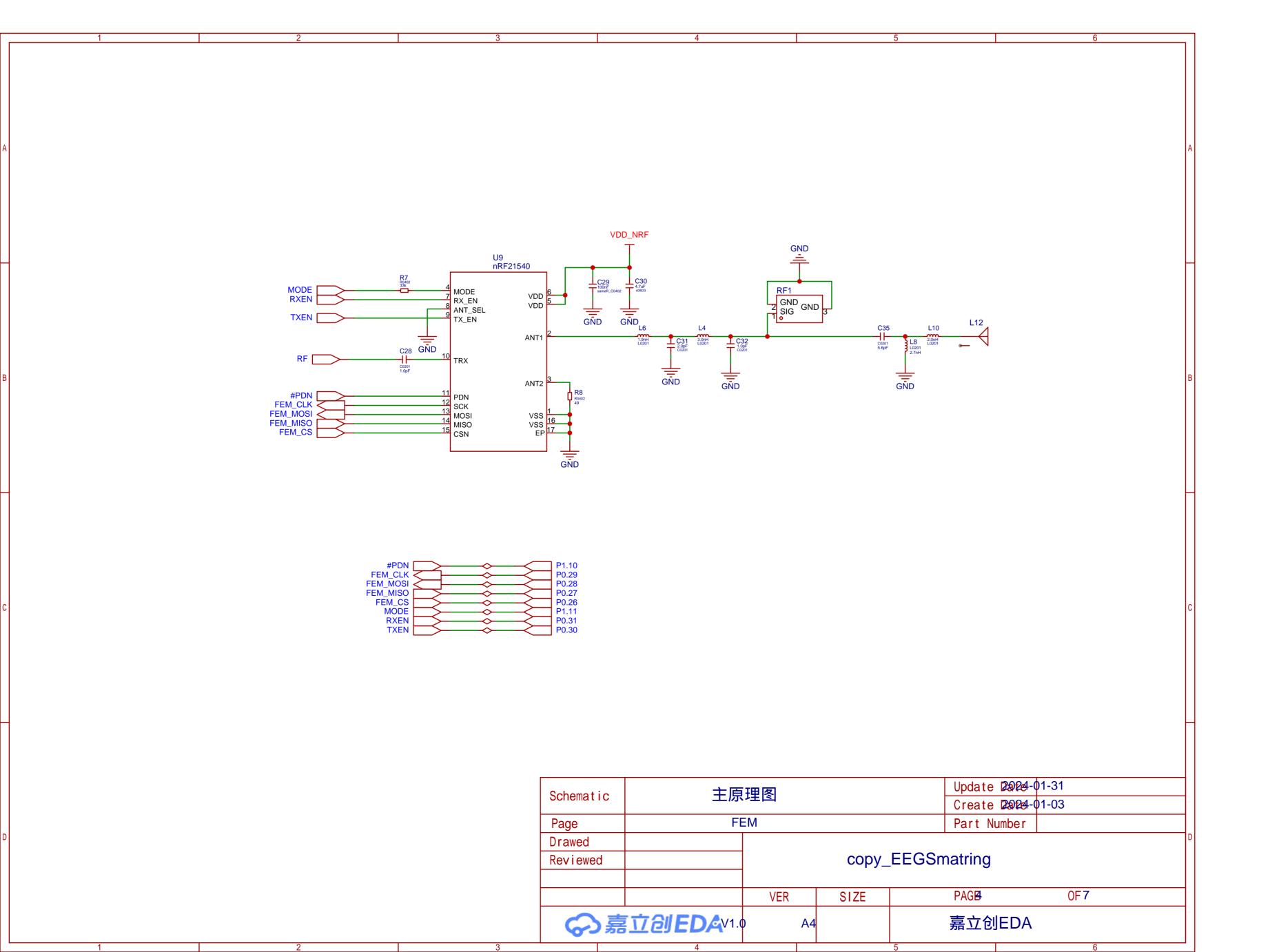


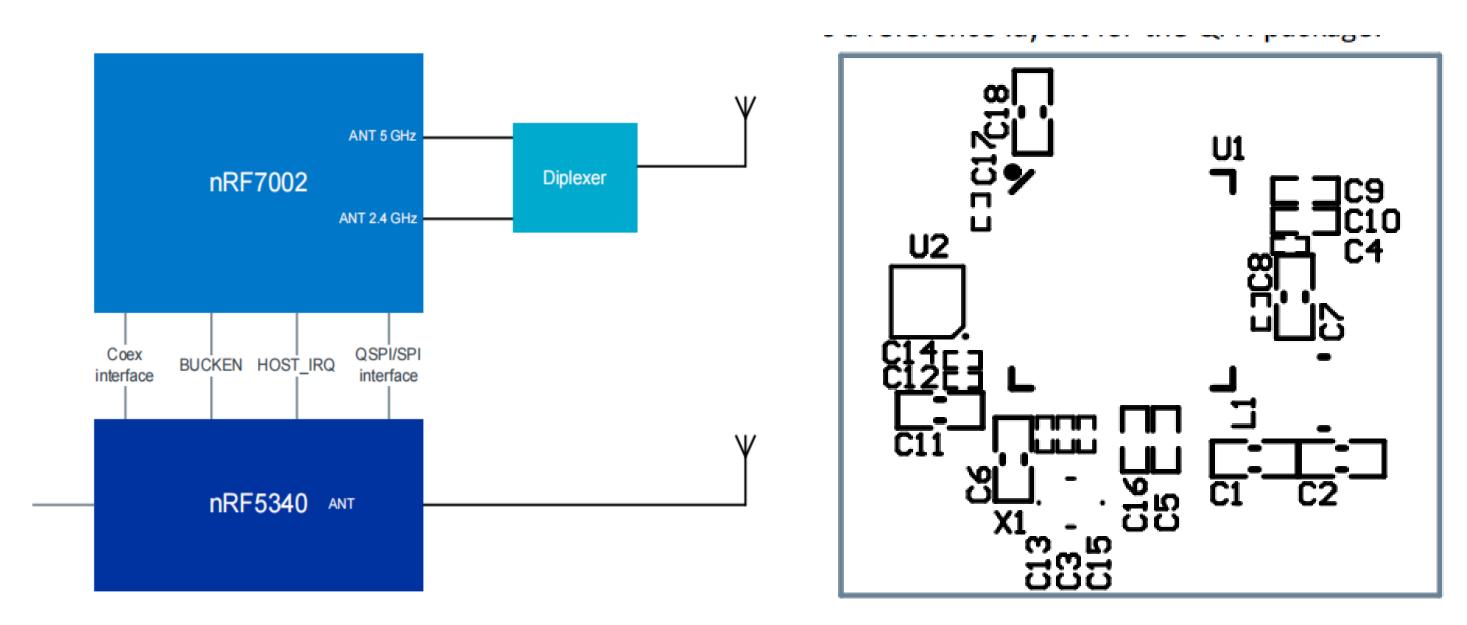
Figure 24. bq241xx PCB Layout





Schematic	主原理图			20	24Updatæ	Date		
Scriematic					2460 <b>ee</b> 13e	Date		
Page	usb data update				Part N	umber		
Drawed								
Reviewed		copy_	EEGSmat	tring				
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<b>○嘉立砂EDA</b> A4			嘉立创EDA					
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	Min.	Max.	Unit
Supply voltages			
VBAT	-0.3	4.5	V
IOVDD	-0.3	3.6	V
I/O pin voltage			
V <sub>I/O</sub> , IOVDD ≤3.3 V	-0.3	IOVDD + 0.3	V
V <sub>I/O</sub> , IOVDD >3.3 V	-0.3	3.6	V
BUCKEN	-0.3	VBAT + 0.3	V
Environmental QFN package			
Storage temperature	-40	125	°C
Moisture Sensitivity Level (MSL)		2	
ESD Human Body Model (HBM)		750	V
ESD Charged Device Model (CDM)		1000	V

Note

Description

Designator Value

U1	nRF7002	Wi-Fi 6 Dual Band companion chip	
U2	2.4 / 5 GHz	WLAN Dual Band Diplexer	
X1	40 MHz	Crystal SMD 1612, 40MHz, Cl=8pF	ESR max 100 ohm
L1	3.3μΗ	Inductor, 1A, ±20%, 200mOhm	
C1, C2, C6, C11	4.7μF	Capacitor, Ceramic, 4.7µF 25V X6S 0603,±10%	Place C1 close to BUCKVBAT pin
			Place C2 close to L1
			Place C11 close to PALDO pin
C3	0.22uF	Capacitor, Ceramic, 0.22μF 10V X5R 0201, ±10%	Place C3 close to RFBUCKVDD pin
C4, C14	0.47uF	Capacitor, Ceramic, 0.47μF 6.3V X5R 0201,±10%	Place C4 close to PWRBUCKVDD pin
C5	1.0μF	Capacitor, Ceramic, 1.0µF 35V X5R 0402,±10%	
C7, C18	2.2μF	Capacitor, Ceramic, 2.2µF 16V X7S 0603,±10%	Place C7 close to BUCKVBATS pin
C8	10nF	Capacitor, Ceramic, 10nF 16V X7R 0201,±10%	
C9	2.2μF	Capacitor, Ceramic, 2.2µF 25V X5R 0201,±10%	
C10	1.0μF	Capacitor, Ceramic, 1.0µF 16V X6S 0402,±10%	
C12	100nF	Capacitor, Ceramic, 100nF 16V X7S 0201,±10%	Place C12 close to PAVDD0 pin
C13	22nF	Capacitor, Ceramic, 22nF 10V X5R 0201,±10%	
C15, C17	2.2μF	Capacitor, Ceramic, 2.2µF 10V X5R 0201,±10%	
C16	1.0μF	Capacitor, Ceramic, 1.0μF 10V X7S 0402,±10%	

